

# P-Channel 100-V (D-S) MOSFET

r-Channel	100-V	(D-9)	INIOSE	_ I

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
- 100	0.18 at V <sub>GS</sub> = - 10 V	- 3	7.9		
- 100	0.2 at V <sub>GS</sub> = - 4.5 V	-2.8	7.9		

#### **FEATURES**

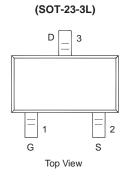
- DT-Trench Power MOSFET
- Ultra Low On-Resistance
- 100 % R<sub>g</sub> Tested 100 % UIS Tested

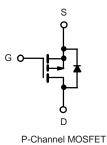


COMPLIANT

### **APPLICATIONS**

• Active Clamp Circuits in DC/DC Power Supplies





<b>ABSOLUTE MAXIMUM RATINGS</b> T	$_{A}$ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 100		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 3.8	- 3	
	T <sub>A</sub> = 70 °C		- 2.5	- 2.8	
Pulsed Drain Current		I <sub>DM</sub>	- 10.6		Α
Continuous Source Current (Diode Conduction) <sup>a, b</sup>		I <sub>S</sub>	- 5	- 6.8	
Single Pulse Avalanche Current	L = 1.0 mH	I <sub>AS</sub>	4.5		
Single Pulse Avalanche Energy	L = 1.0 mm	E <sub>AS</sub>		1.01	mJ
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.25 0.75 0.8 0.48		W
	T <sub>A</sub> = 70 °C	' D			v V
Operating Junction and Storage Temperature Rang	e	T <sub>J</sub> , T <sub>stg</sub>	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	<b>D</b>	75	100	
	Steady State	$R_{thJA}$	120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	40	50	]

#### Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.



			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 100			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 1.2		- 2.5		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	l	V <sub>DS</sub> = - 150 V, V <sub>GS</sub> = 0 V	- 150 V, V <sub>GS</sub> = 0 V		- 1		
	IDSS	V <sub>DS</sub> = - 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -15 \text{ V}, V_{GS} = 10 \text{ V}$	- 2.6			Α	
5	В	$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	0.18				
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 0.5 A		0.2		Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 0.5 A		2.2		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = - 1.0 A, V <sub>GS</sub> = 0 V		0.7	- 1.2	V	
Dynamic <sup>b</sup>			•				
Total Gate Charge	$Q_g$	V 75 V V 10 V		7.7	12		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -75 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} \cong -0.5 \text{ A}$		1.5		nC	
Gate-Drain Charge	$Q_{gd}$	1 <sub>D</sub> = 0.0 /1		2.5			
Gate Resistance	$R_g$	f = 1.0 MHz		9		Ω	
Input Capacitance	C <sub>iss</sub>			340	510		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		30		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			16			
Switching <sup>c</sup>							
T	t <sub>d(on)</sub>	V 75 V B 75 0		7	11		
Turn-On Time	t <sub>r</sub>	$V_{DD} = -75 \text{ V, } R_L = 75 \Omega$ $I_D \cong -1.0 \text{ A, } V_{GEN} = -10 \text{ V}$		11	17	ns	
Turn-Off Time	t <sub>d(off)</sub>	$R_{a} = 6 \Omega$		16	25	113	
	t <sub>f</sub>	. ·y =		11	17		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		90	135	nC	

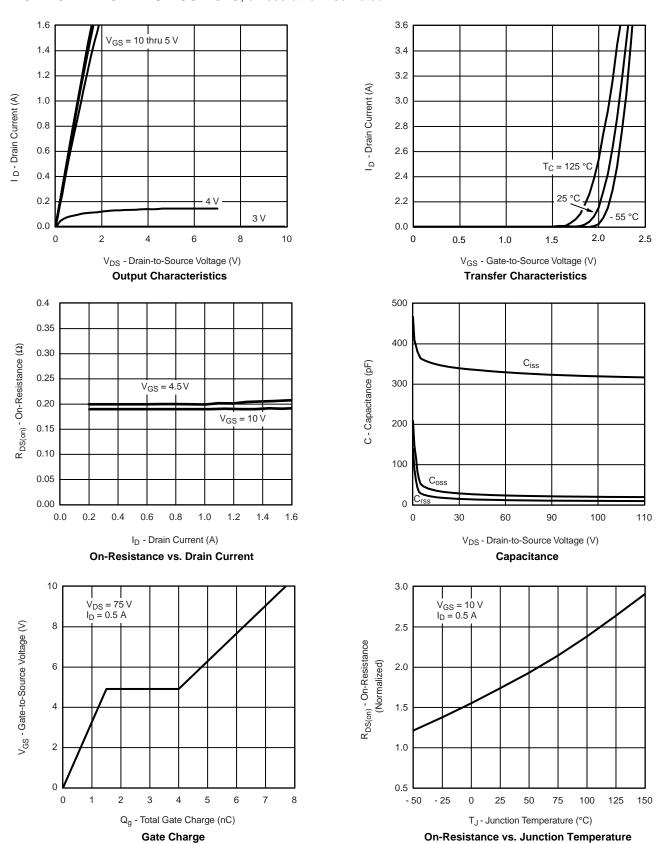
#### Notes:

- a. Pulse test: PW  $\leq$  300 µs duty cycle  $\leq$  2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

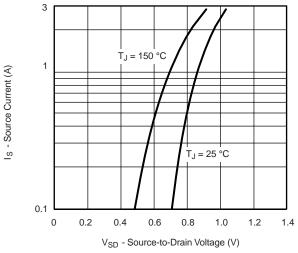


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

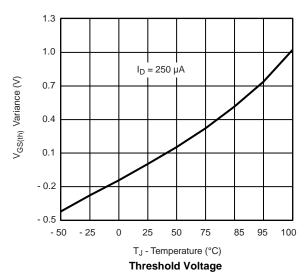


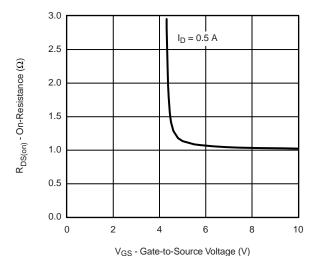


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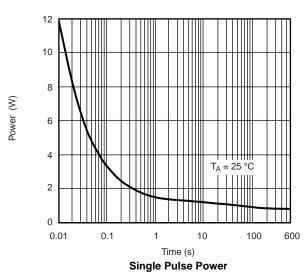


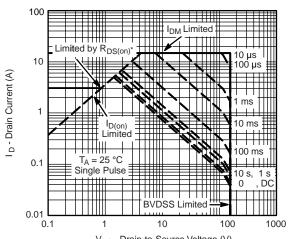
#### Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage



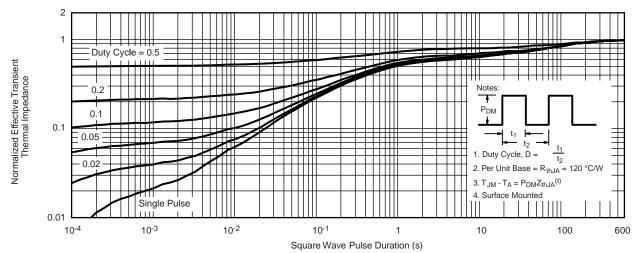


 $V_{DS} \mbox{ - Drain-to-Source Voltage (V)} \\ ^*V_{GS} \mbox{ > minimum } V_{GS} \mbox{ at which } R_{DS(on)} \mbox{ is specified}$ 

Safe Operating Area



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

DIMENSIONS IN INCHES

NOM

0.039

0.016

MAX

0.049

0.005

0.045

0.020

0.008

0.122

0.118

0.071

0.024

8°

MIN

0.033

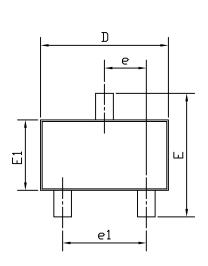
0.000

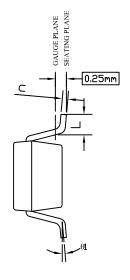
0.028

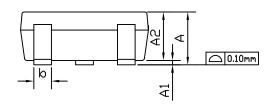
0.012



#### SOT-23-3L PACKAGE OUTLINE







SYMBOLS

**A**1

A2

b

MIN

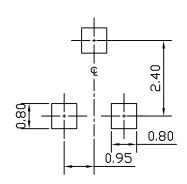
0.85

0.00

0.70

0.30

#### RECOMMENDED LAND PATTERN



0.08 0.13 0.20 0.003 0.005 2.80 2.90 D 3.10 0.110 0.114 2.80 Е 2.60 3.00 0.102 0.110 E1 1.60 1.80 0.055 0.063 1.40 0.95 BSC 0.037 BSC e 1.90 BSC 0.075 BSC e1 0.30 0.60 0.012 L θ1 0° 8° 0°

DIMENSIONS IN MILLIMETERS

NOM

1.00

0.40

MAX

1.25

0.13

1.15

0.50

UNIT: mm

#### NOTE

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS.
  MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
- 2. TOLERANCE  $\pm 0.100$  mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- 3. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.





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